

## **AMENDMENTS TO THE CLAIMS**

The following listing of claims will replace all prior versions and listings of claims in the application.

### **LISTING OF CLAIMS**

1. (Currently Amended) A method of producing an acoustic resonator device, comprising:

depositing a first metal film directly on a substrate;

patterning said first metal film;

depositing piezoelectric material on said first metal film to form a single, continuous piezoelectric layer;

depositing a second metal film on said single piezoelectric material layer;

patterning said second metal film; and

removing some or all piezoelectric material from said single piezoelectric layer not involved in signal transmission by a selective etching process to limit lateral propagation losses to un-etched regions of the acoustic resonator device, said removing step being performed after said second metal film is patterned.

2-9 (Canceled)

10. (Original) The method of claim 1, wherein said piezoelectric material is selected from the group comprising at least AlN, ZnO and CdS.

11. (Previously Presented) The method of claim 1, wherein said first and second metal films are formed by lithographic patterning of Al metal or other conductors.

12. (Currently Amended) The method of claim 1, wherein said substrate is formed as a plurality of acoustic reflecting layers on a substrate formed from one of such as a silicon, quartz, or glass wafer.

13. (Currently Amended) A method of isolating an acoustic resonator device, comprising:

depositing a first metal film directly on a substrate;

depositing piezoelectric material on said first metal film to form a single, continuous piezoelectric layer;

depositing a second metal film on said single piezoelectric material layer; and

removing some or all piezoelectric material from said single piezoelectric layer not involved in signal transmission with a selective etching process to limit propagation of energy in lateral modes, said removing step being performed after said second metal film is deposited on said single piezoelectric material layer.

14. (Canceled)

15. (Previously Presented) The method of claim 13, wherein at least some of the substrate surface is removed by selective etching.

16. (Original) The method of claim 13, wherein at least some of the removed piezoelectric material forms a void which is back filled with a different material.

Claims 17-29 (Canceled)

30. (Previously Presented) The method of claim 291, wherein the continuous piezoelectric layer is not patterned or etched until the removing step.

31. (Canceled)

32. (Previously Presented) The method of claim 3113, wherein the continuous piezoelectric layer is not patterned or etched until the removing step.